

## MJE340

### High Voltage General Purpose Applications

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to MJE350



### NPN Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	300	V
$V_{CEO}$	Collector-Emitter Voltage	300	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	500	mA
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1\text{mA}, I_B = 0$	300		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 300\text{V}, I_E = 0$		100	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{BE} = 3\text{V}, I_C = 0$		100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	30	240	

# Typical Characteristics

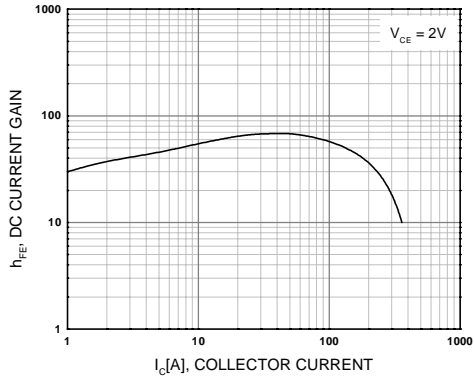


Figure 1. DC current Gain

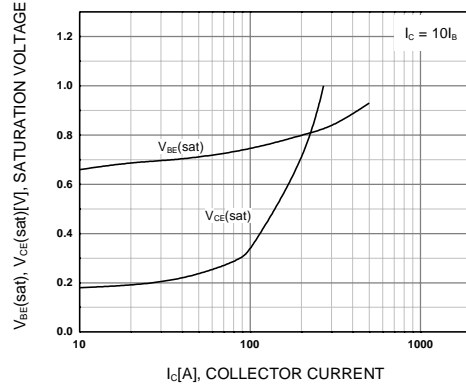


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

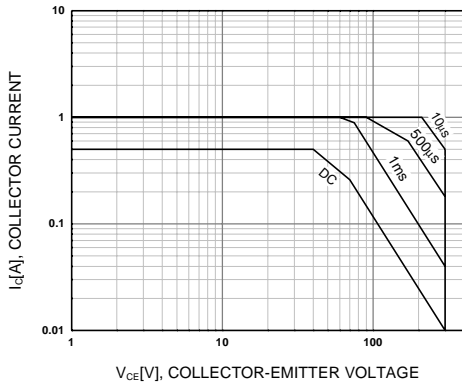


Figure 3. Safe Operating Area

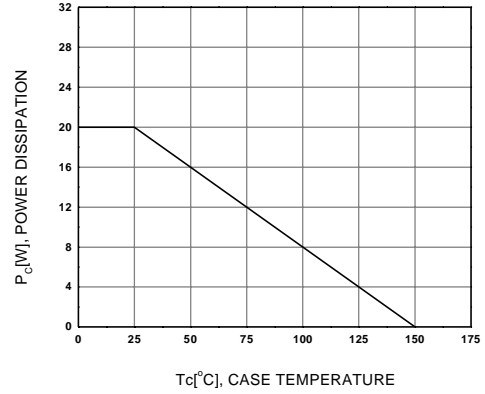


Figure 4. Power Derating

# Package Dimensions

## TO-126



Dimensions in Millimeters

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NPN Epitaxial Silicon Transistor

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Features

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[Product status/pricing/packaging](#)

Product	Product status	Pricing*	Package type	Leads	Packing method
MJE340STU	Full Production	\$0.174	<a href="#">TO-126</a>	3	RAIL

\* 1,000 piece Budgetary Pricing

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